

ABSTRACT OF THE DISCLOSURE

A flash memory device with selective gate within a substrate and method of fabricating the same. The flash memory device comprises a substrate with a floating gate disposed thereon. A wordline extends along a first direction and overlies the floating gate and the adjacent substrate thereof. A trench is disposed in the substrate adjacent to one side of the wordline. A selective gate is vertically disposed in the trench, partially covering the floating gate. A source region is disposed in the substrate adjacent to the other side of the wordline and a drain region is disposed in the substrate beneath the selective gate.